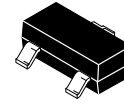
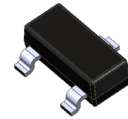


# Diode – Small Signal

## MMBD1501A, MMBD1503A, MMBD1504A, MMBD1505A



SOT-23 (TO-236)  
CASE 318-08



SOT-23  
CASE 318BM

### ABSOLUTE MAXIMUM RATINGS

(Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.) (Notes 1, 2)

Symbol	Parameter	Value	Unit
$V_{RRM}$	Maximum Repetitive Reverse Voltage	200	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	Pulse Width = 1.0 s	1.0
		Pulse Width = 1.0 $\mu\text{s}$	2.0
$T_{STG}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- These ratings are based on a maximum junction temperature of  $150^\circ\text{C}$ .
- These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty-cycle operations.

### THERMAL CHARACTERISTICS

(Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.)

Symbol	Parameter	Value	Unit
$P_D$	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	$^\circ\text{C}/\text{W}$

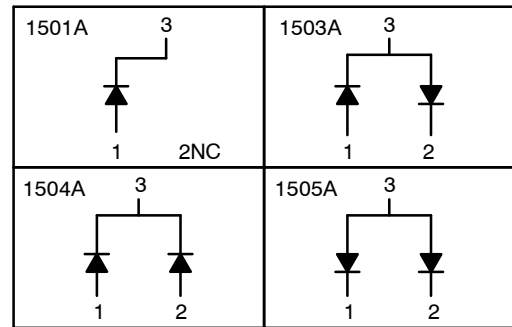
### ELECTRICAL CHARACTERISTICS

(Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.)

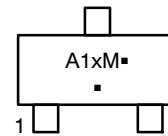
Symbol	Parameter	Conditions	Min	Max	Unit
$V_R$	Breakdown Voltage	$I_R = 5.0 \mu\text{A}$	200	-	V
$V_F$	Forward Voltage	$I_F = 1.0 \text{ mA}$	620	720	mV
		$I_F = 10 \text{ mA}$	720	830	mV
		$I_F = 50 \text{ mA}$	800	890	mV
		$I_F = 100 \text{ mA}$	830	930	mV
		$I_F = 200 \text{ mA}$	0.87	1.10	V
		$I_F = 300 \text{ mA}$	0.90	1.15	V
$I_R$	Reverse Current	$V_R = 125 \text{ V}$	-	1.0	nA
		$V_R = 125 \text{ V}$ , $T_A = 150^\circ\text{C}$	-	3.0	$\mu\text{A}$
		$V_R = 180 \text{ V}$	-	10.0	nA
		$V_R = 180 \text{ V}$ , $T_A = 150^\circ\text{C}$	-	5.0	$\mu\text{A}$
$C_T$	Total Capacitance	$V_R = 0$ , $f = 1.0 \text{ MHz}$	-	4.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### CONNECTION DIAGRAMS



### MARKING DIAGRAM



- A1x = Specific Device Code  
x = 1, 3, 4, 5
- M = Date Code
- = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

TYPICAL CHARACTERISTICS

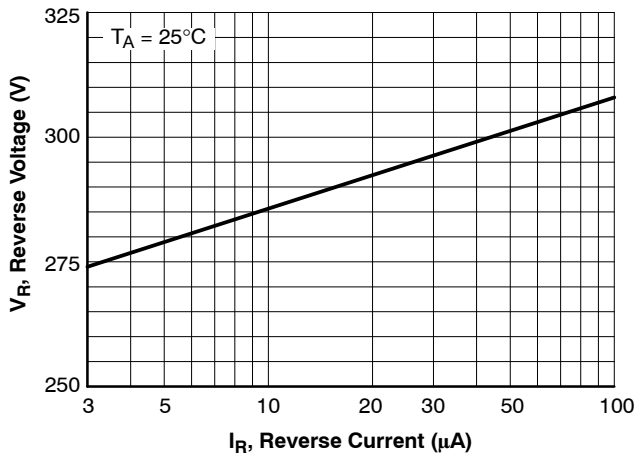


Figure 1. Reverse Voltage vs. Reverse Current  
 $I_R - 3.0$  to  $100 \mu\text{A}$

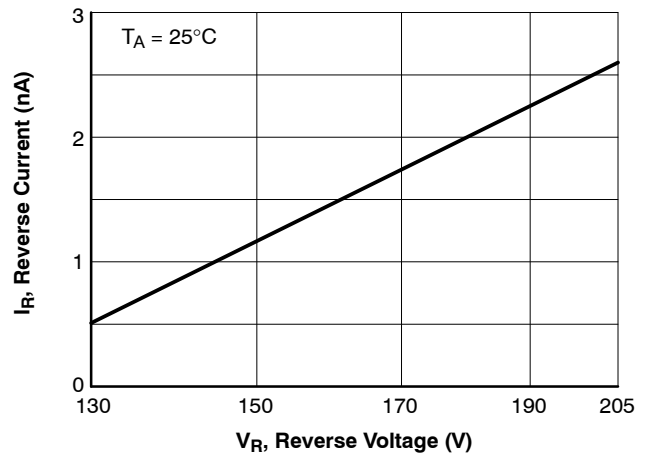


Figure 2. Reverse Current vs. Reverse Voltage  
 $V_R - 130$  to  $205 \text{ V}$

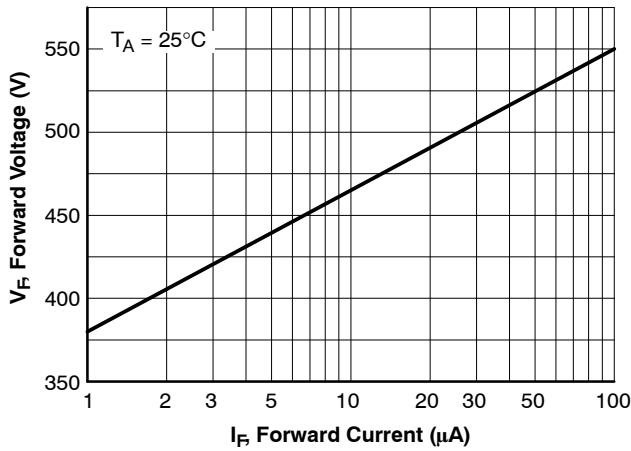


Figure 3. Forward Voltage vs. Forward Current  
 $I_F - 1$  to  $100 \mu\text{A}$

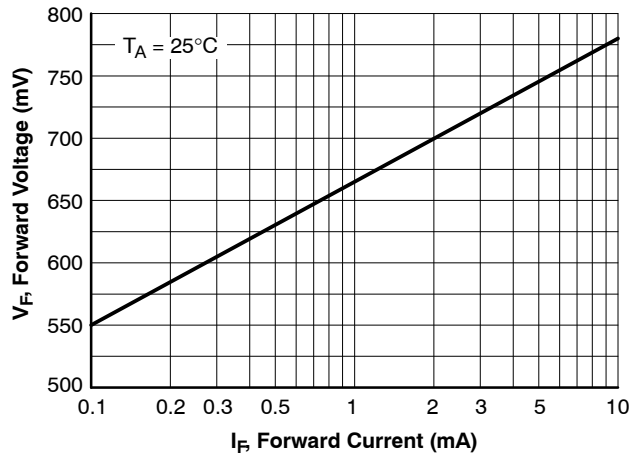


Figure 4. Forward Voltage vs. Forward Current  
 $I_F - 0.1$  to  $10 \text{ mA}$

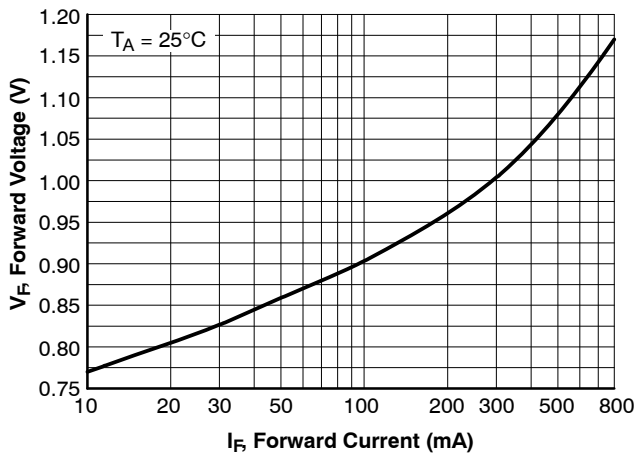


Figure 5. Forward Voltage vs. Forward Current  
 $I_F - 10$  to  $800 \text{ mA}$

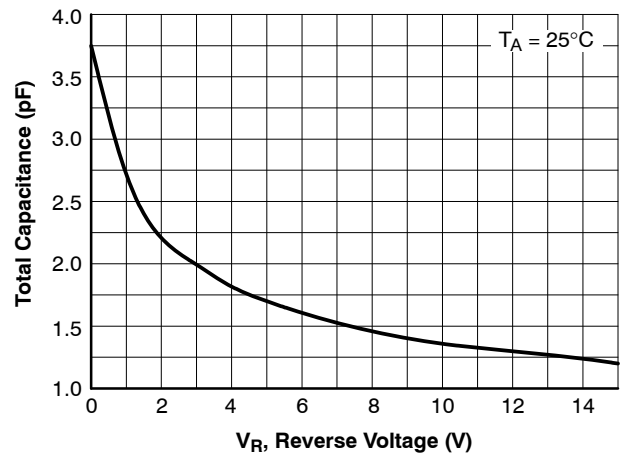


Figure 6. Total Capacitance vs. Reverse Voltage  
 $V_R - 0$  to  $15 \text{ V}$

# MMBD1501A, MMBD1503A, MMBD1504A, MMBD1505A

## TYPICAL CHARACTERISTICS (Continued)

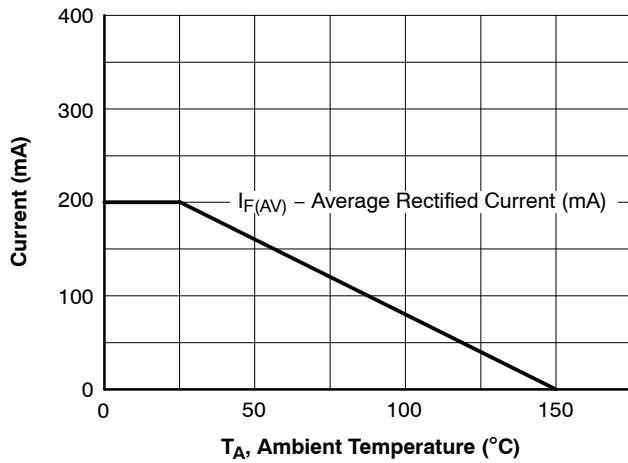


Figure 7. Average Rectified Current ( $I_{F(AV)}$ ) vs. Ambient Temperature ( $T_A$ )

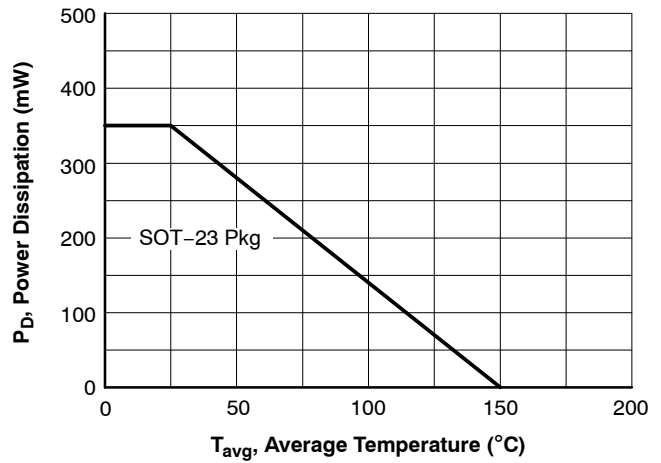


Figure 8. Power Derating Curve

### ORDERING INFORMATION

Part Number	Specific Device Marking	Package Type	Shipping <sup>†</sup>
MMBD1501A	A11	SOT-23 (TO-236) (Pb-Free)	3,000 / Tape & Reel (7")
MMBD1503A	A13		
MMBD1503A_D87Z	A13	SOT-23 (Pb-Free)	10,000 / Tape & Reel (13")
MMBD1504A	A14	SOT-23 (TO-236) (Pb-Free)	3,000 / Tape & Reel (7")
MMBD1505A	A15		
NSVMMBD1501ALT3G	A11		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



### SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

### RECOMMENDED SOLDERING FOOTPRINT



### GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:  
CANCELLED

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 7:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 8:  
PIN 1. ANODE  
2. NO CONNECTION  
3. CATHODE

STYLE 9:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 10:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 13:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 14:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 15:  
PIN 1. GATE  
2. CATHODE  
3. ANODE

STYLE 16:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE

STYLE 17:  
PIN 1. NO CONNECTION  
2. ANODE  
3. CATHODE

STYLE 18:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. ANODE

STYLE 19:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE-ANODE

STYLE 20:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 22:  
PIN 1. RETURN  
2. OUTPUT  
3. INPUT

STYLE 23:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 24:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 25:  
PIN 1. ANODE  
2. CATHODE  
3. GATE

STYLE 26:  
PIN 1. CATHODE  
2. ANODE  
3. NO CONNECTION

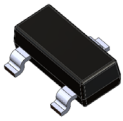
STYLE 27:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

STYLE 28:  
PIN 1. ANODE  
2. ANODE  
3. ANODE

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

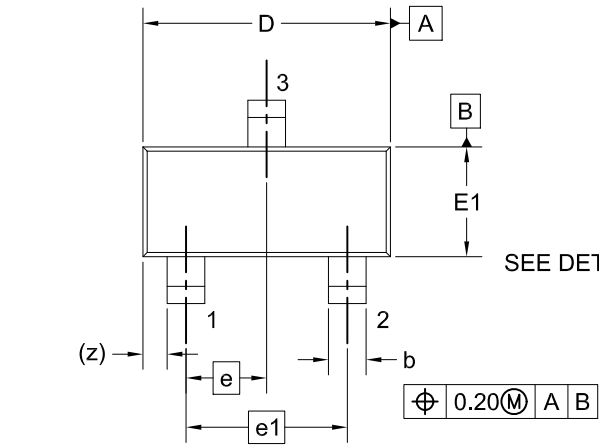


**SOT-23**  
**CASE 318BM**  
**ISSUE A**

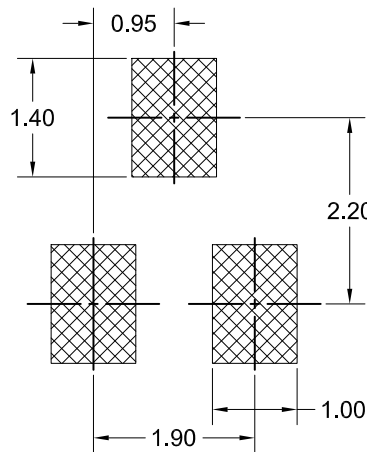
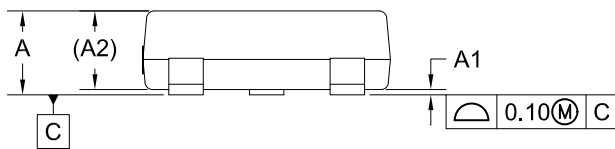
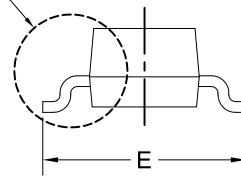
DATE 01 SEP 2021

NOTES: UNLESS OTHERWISE SPECIFIED

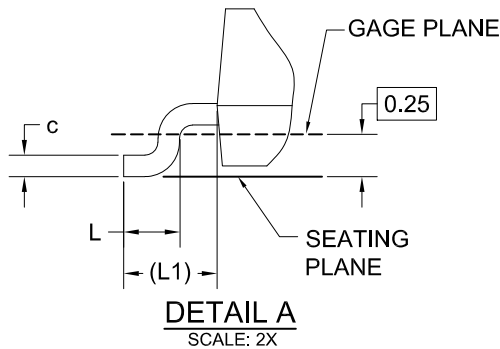
- A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 2009.



SEE DETAIL A

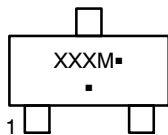


DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.20
A1	0.00	0.05	0.10
A2	0.93 REF		
b	0.37	0.44	0.60
c	0.08	0.15	0.23
D	2.72	2.92	3.12
E	2.10	2.40	2.70
E1	1.15	1.30	1.50
e	0.95 BSC		
e1	1.90 BSC		
L	0.20	---	---
L1	0.55 REF		
z	0.29 REF		



LAND PATTERN  
RECOMMENDATION

### GENERIC MARKING DIAGRAM\*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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